PZTA92T1G, NSVPZTA92T1G

High Voltage Transistor

PNP Silicon

Features

- Complement to PZTA42T1G
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS ($T_C = 25^{\circ}C$ unless otherwise noted)

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V _{CEO}	-300	Vdc
Collector-Base Voltage	V _{CBO}	-300	Vdc
Emitter-Base Voltage	V _{EBO}	-5.0	Vdc
Collector Current	Ic	-500	mAdc
Total Power Dissipation up to @ T _A = 25°C (Note 1)	P _D	1.5	W
Storage Temperature Range	T _{stg}	-65 to +150	°C
Junction Temperature	TJ	150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Device mounted on a FR-4 glass epoxy printed circuit board 1.575 in x 1.575 in x 0.0625 in; mounting pad for the collector lead = 0.93 sq in.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction–to–Ambient (Note 2)	$R_{\theta JA}$	83.3	°C/W

Device mounted on a FR-4 glass epoxy printed circuit board
 1.575 in x 1.575 in x 0.0625 in; mounting pad for the collector lead = 0.93 sq in.



ON Semiconductor®

www.onsemi.com

SOT-223 PACKAGE PNP SILICON HIGH VOLTAGE TRANSISTOR SURFACE MOUNT

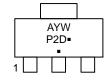
COLLECTOR 2,4

BASE
1

EMITTER 3



MARKING DIAGRAM



P2D = Specific Device Code A = Assembly Location

Y = Year

W = Work Week ■ Pb–Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
PZTA92T1G, NSVPZTA92T1G	SOT-223 (Pb-Free)	1,000 / Tape & Reel
NSVPZTA92T3G	SOT-223 (Pb-Free)	4,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristics	Symbol	Min	Max	Unit
OFF CHARACTERISTICS	•	•		
Collector–Emitter Breakdown Voltage (Note 3) $(I_C = -1.0 \text{ mAdc}, I_B = 0)$	V _{(BR)CEO}	-300	_	Vdc
Collector–Base Breakdown Voltage ($I_C = -100 \mu Adc$, $I_E = 0$)	V _{(BR)CBO}	-300	_	Vdc
Emitter–Base Breakdown Voltage $(I_E = -100 \mu Adc, I_C = 0)$	V _{(BR)EBO}	-5.0	-	Vdc
Collector-Base Cutoff Current $(V_{CB} = -200 \text{ Vdc}, I_E = 0)$	I _{CBO}	_	-0.25	μAdc
Emitter–Base Cutoff Current $(V_{BE} = -3.0 \text{ Vdc}, I_C = 0)$	I _{EBO}	-	-0.1	μAdc
ON CHARACTERISTICS	•	•	•	•
DC Current Gain	h _{FE}	25 40 40	- - -	-
Saturation Voltages ($I_C = -20 \text{ mAdc}$, $I_B = -2.0 \text{ mAdc}$) ($I_C = -20 \text{ mAdc}$, $I_B = -2.0 \text{ mAdc}$)	V _{CE(sat)} V _{BE(sat)}	- -	-0.5 -0.9	Vdc
DYNAMIC CHARACTERISTICS	•	•	1	•
Collector–Base Capacitance @ f = 1.0 MHz $(V_{CB} = -20 \text{ Vdc}, I_E = 0)$	C _{cb}	_	6.0	pF
Current–Gain – Bandwidth Product $(I_C = -10 \text{ mAdc}, V_{CE} = -20 \text{ Vdc}, f = 100 \text{ MHz})$	f _T	50	_	MHz

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

^{3.} Pulse Test Conditions, t_p = 300 μ s, δ 0.02.

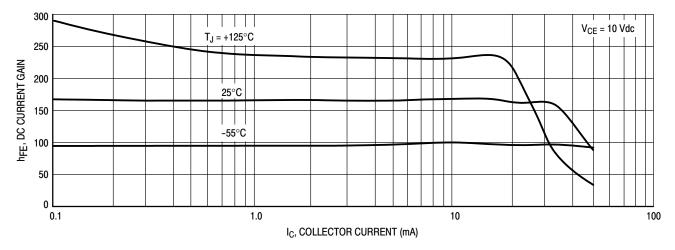
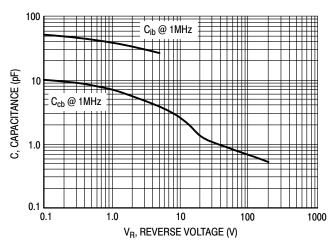


Figure 1. DC Current Gain

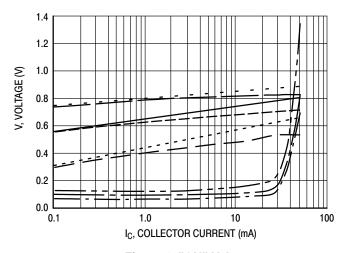
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 f_T , CURRENT-GAIN — BANDWIDTH (MHz) 130 110 90 70 50 $T_J = 25^{\circ}C$ V_{CE} = 20 Vdc 30 F = 20 MHz 10 3 11 13 15 17 19 1 IC, COLLECTOR CURRENT (mA)

Figure 2. Capacitance

Figure 3. Current-Gain - Bandwidth



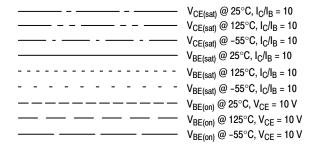


Figure 4. "ON" Voltages

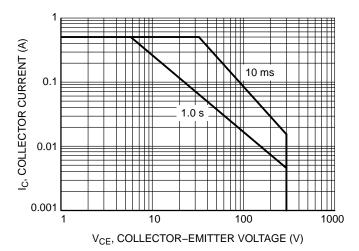
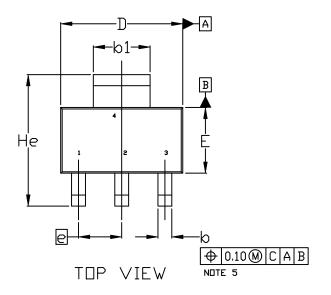


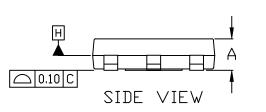
Figure 5. Safe Operating Area

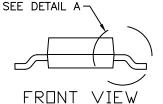


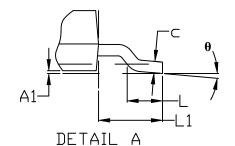
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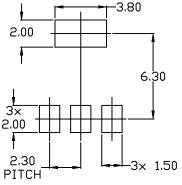




NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. DIMENSIONS D & E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
 MOLD FLASH, PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.200MM PER SIDE.
- 4. DATUMS A AND B ARE DETERMINED AT DATUM H.
- 5. ALLIS DEFINED AS THE VERTICAL DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT OF THE PACKAGE BODY.
- 6. POSITIONAL TOLERANCE APPLIES TO DIMENSIONS 6 AND 61.

	MILLIMETERS			
DIM	MIN.	N□M.	MAX.	
Α	1.50	1.63	1.75	
A1	0.02	0.06	0.10	
Ø	0.60	0.75	0.89	
b1	2.90	3.06	3.20	
U	0.24	0.29	0.35	
D	6.30	6.50	6.70	
E	3.30	3.50	3.70	
е	2.30 BSC			
L	0.20			
L1	1.50	1.75	2.00	
He	6.70	7.00	7.30	
θ	0°		10°	



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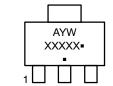
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DATE 02 OCT 2018

STYLE 1: PIN 1. BASE 2. COLLECTOR 3. EMITTER 4. COLLECTOR	STYLE 2: PIN 1. ANODE 2. CATHODE 3. NC 4. CATHODE	STYLE 3: PIN 1. GATE 2. DRAIN 3. SOURCE 4. DRAIN	STYLE 4: PIN 1. SOURCE 2. DRAIN 3. GATE 4. DRAIN	STYLE 5: PIN 1. DRAIN 2. GATE 3. SOURCE 4. GATE
STYLE 6: PIN 1. RETURN 2. INPUT 3. OUTPUT 4. INPUT	STYLE 7: PIN 1. ANODE 1 2. CATHODE 3. ANODE 2 4. CATHODE	STYLE 8: CANCELLED	STYLE 9: PIN 1. INPUT 2. GROUND 3. LOGIC 4. GROUND	STYLE 10: PIN 1. CATHODE 2. ANODE 3. GATE 4. ANODE
STYLE 11: PIN 1. MT 1 2. MT 2 3. GATE 4. MT 2	STYLE 12: PIN 1. INPUT 2. OUTPUT 3. NC 4. OUTPUT	STYLE 13: PIN 1. GATE 2. COLLECTOR 3. EMITTER 4. COLLECTOR		

GENERIC MARKING DIAGRAM*



A = Assembly Location

Y = Year W = Work Week

not follow the Generic Marking.

XXXXX = Specific Device Code

= Pb-Free Package

(Note: Microdot may be in either location)
*This information is generic. Please refer to
device data sheet for actual part marking.
Pb-Free indicator, "G" or microdot "•", may
or may not be present. Some products may

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